

6N70

Power MOSFET

6.0A, 700V N-CHANNEL POWER MOSFET

■ DESCRIPTION

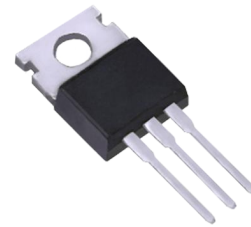
The UTC **6N70** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with a minimum on-state resistance, high switching speed, low gate charge and low input capacitance.

The UTC **6N70** is universally applied in high efficiency switch mode power supply.

■ FEATURES

* $R_{DS(ON)} < 1.8\Omega$ @ $V_{GS}=10V$, $I_D=3A$

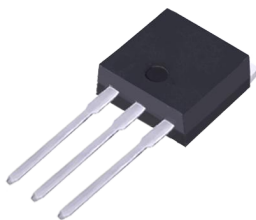
* High switching speed



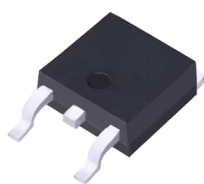
TO-220



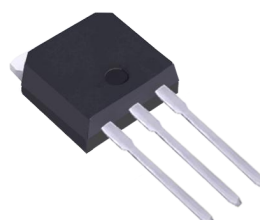
TO-220F



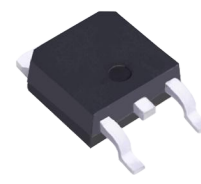
TO-262



TO-263



TO-251



TO-252

■ ABSOLUTE MAXIMUM RATINGS (unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V_{DSS}	700	V	
Gate-Source Voltage (Note 2)		V_{GSS}	± 30	V	
Drain Current	Continuous	I_D	$T_C=25^\circ\text{C}$	6	A
			$T_C=100^\circ\text{C}$	3.8	A
	Pulsed	I_{DM}	24	A	
Avalanche Current (Note 2)		I_{AR}	6	A	
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	582	mJ	
	Repetitive (Note 2)	E_{AR}	13	mJ	
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.5	V/ns	
Power Dissipation	TO-220F1	P_D	42	W	
	TO-220F2				
	TO-220F		40		
	TO-262/ TO-263		125		
Linear Derating Factor	TO-220F1	P_D	0.33	W/ $^\circ\text{C}$	
	TO-220F2				
	TO-220F		0.32		
	TO-262/TO-263		1		
Junction Temperature		T_J	+150	$^\circ\text{C}$	
Storage Temperature		T_{STG}	-55~+150	$^\circ\text{C}$	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 30\text{mH}$, $I_{AS} = 6\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 27\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 6\text{A}$, $di/dt \leq 140\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220F1	θ_{JC}	2.9	$^\circ\text{C}/\text{W}$
	TO-220F2			
	TO-220F		3.1	$^\circ\text{C}/\text{W}$
	TO-262/TO-263		1.0	$^\circ\text{C}/\text{W}$
	TO-263		1.0	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	700			V
Breakdown Voltage Temperature Coefficient		$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\mu\text{A}$		0.79		$\text{V}/^\circ\text{C}$
Drain-Source Leakage Current		I_{DSS}	$V_{DS}=700\text{V}$			25	μA
			$V_{DS}=560\text{V}$, $T_C=125^\circ\text{C}$			250	μA
Gate-Source Leakage Current	Forward	I_{GSS}	$V_{GS}=+30\text{V}$, $V_{DS}=0\text{V}$			+100	nA
	Reverse		$V_{GS}=-30\text{V}$, $V_{DS}=0\text{V}$			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$, $V_{DS}=5\text{V}$	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=3\text{A}$ (Note 1)		1.5	1.8	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$ (Note 1, 2)		900	1200	pF
Output Capacitance		C_{OSS}			90	115	pF
Reverse Transfer Capacitance		C_{RSS}			18	55	pF
SWITCHING PARAMETERS							
Turn-ON Delay Time		$t_{D(ON)}$	$V_{DD}=350\text{V}$, $I_D=6\text{A}$, $R_G=11.5\Omega$		40	70	ns
Rise Time		t_R			65	90	ns
Turn-OFF Delay Time		$t_{D(OFF)}$			190	230	ns
Fall-Time		t_F			88	116	ns
Total Gate Charge		Q_G	$V_{GS}=10\text{V}$, $V_{DS}=560\text{V}$, $I_D=6\text{A}$ (Note 1, 2)		110	140	nC
Gate to Source Charge		Q_{GS}			9		nC
Gate to Drain Charge		Q_{GD}			23.1		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S	Integral reverse pn-diode in the MOSFET			6	A
Maximum Body-Diode Pulsed Current (Note 3)		I_{SM}				24	A
Drain-Source Diode Forward Voltage (Note 2)		V_{SD}	$I_S=6\text{A}$, $V_{GS}=0\text{V}$, $T_J = 25^\circ\text{C}$			1.4	V
Body Diode Reverse Recovery Time		t_{rr}	$I_F=6\text{A}$, $dI_F/dt=100\text{A}/\mu\text{s}$, $T_J = 25^\circ\text{C}$		440		ns
Body Diode Reverse Recovery Charge		Q_{RR}			4.05		μC

Notes: 1. Pulse Test: Pulse width $\leq 250\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

3. Repetitive Rating: Pulse width limited by maximum junction temperature

■ TYPICAL CHARACTERISTICS

